

# July 2007 **IGBT**®

# FGL40N120AN 1200V NPT IGBT

#### **Features**

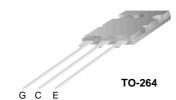
- · High speed switching
- Low saturation voltage :  $V_{CE(sat)} = 2.6 \text{ V} @ I_C = 40 \text{A}$
- High input impedance

### **Applications**

Induction Heating, UPS, AC & DC motor controls and general purpose inverters.

## **Description**

Employing NPT technology, Fairchild's AN series of IGBTs provides low conduction and switching losses. The AN series offers an solution for application such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).





## **Absolute Maximum Ratings**

Symbol	Parameter		FGL40N120AN	Units	
V <sub>CES</sub>	Collector-Emitter Voltage		1200	V	
V <sub>GES</sub>	Gate-Emitter Voltage		±25	V	
	Collector Current	@T <sub>C</sub> = 25°C	64	A	
I <sub>C</sub>	Collector Current	@T <sub>C</sub> = 100°C	40	А	
I <sub>CM(1)</sub>	Pulsed Collector Current		160	A	
D	Maximum Power Dissipation	@T <sub>C</sub> = 25°C	500	W	
$P_D$	Maximum Power Dissipation	@T <sub>C</sub> = 100°C	200	W	
SCWT	Short Circuit Withstand Time, V <sub>CE</sub> = 600V, V <sub>GE</sub> = 15V, T <sub>C</sub> = 125°C		10	μs	
T <sub>J</sub>	Operating Junction Temperature		-55 to +150	°C	
T <sub>STG</sub>	Storage Temperature Range		-55 to +150	°C	
T <sub>L</sub>	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 second	ls	300	°C	

#### Notes:

(1) Pulse width limited by max. junction temperature

#### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction-to-Case		0.25	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		25	°C/W

# **Package Marking and Ordering Information**

<b>Device Marking</b>	Device	Package	Reel Size	Tape Width	Quantity
FGL40N120AN	FGL40N120AN	TO-264	=	=	25

# Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Off Charact	eristics					
BV <sub>CES</sub>	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V$ , $I_C = 1mA$	1200			V
BV <sub>CES</sub> / ΔT <sub>J</sub>	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V$ , $I_C = 1mA$		0.6		V/°C
I <sub>CES</sub>	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$			1	mA
I <sub>GES</sub>	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$			±250	nA
On Charact	eristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	$I_{C} = 250 \mu A, V_{CE} = V_{GE}$	3.5	5.5	7.5	V
OL(III)	0	I <sub>C</sub> = 40A, V <sub>GE</sub> = 15V		2.6	3.2	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 40A, V <sub>GE</sub> = 15V, T <sub>C</sub> = 125°C		2.9		V
	-	I <sub>C</sub> = 64A, V <sub>GE</sub> = 15V		3.15		V
Dynamic Cl	naracteristics	,		l	•	
C <sub>ies</sub>	Input Capacitance			3200		pF
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 30V, V_{GE} = 0V$		370		pF
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1MHz		125		pF
Switching (	Characteristics			•		•
t <sub>d(on)</sub>	Turn-On Delay Time			15		ns
t <sub>r</sub>	Rise Time			20		ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 600V, I_{C} = 40A,$ $R_{G} = 5\Omega, V_{GE} = 15V,$		110		ns
t <sub>f</sub>	Fall Time			40	80	ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 25°C		2.3	3.45	mJ
E <sub>off</sub>	Turn-Off Switching Loss			1.1	1.65	mJ
E <sub>ts</sub>	Total Switching Loss			3.4	5.1	mJ
t <sub>d(on)</sub>	Turn-On Delay Time			20		ns
t <sub>r</sub>	Rise Time			25		ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 600V, I_{C} = 40A,$		120		ns
t <sub>f</sub>	Fall Time	$R_G = 5\Omega$ , $V_{GE} = 15V$ ,		45		ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 125°C		2.5		mJ
E <sub>off</sub>	Turn-Off Switching Loss			1.8		mJ
E <sub>ts</sub>	Total Switching Loss			4.3		mJ
Qg	Total Gate charge	V 000V I 101		220	330	nC
Q <sub>ge</sub>	Gate-Emitter Charge	$V_{CE} = 600V, I_{C} = 40A,$ $V_{GE} = 15V$		25	38	nC
Q <sub>gc</sub>	Gate-Collector Charge	· GE = 10 *		130	195	nC

## **Typical Performance Characteristics**

**Figure 1. Typical Output Characteristics** 

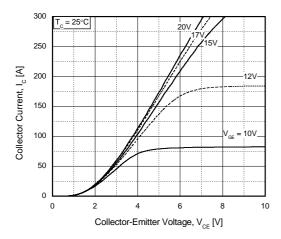


Figure 3. Saturation Voltage vs. Case
Temperature at Variant Current Level

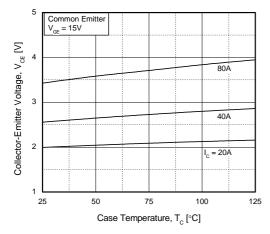


Figure 5. Saturation Voltage vs. V<sub>GE</sub>

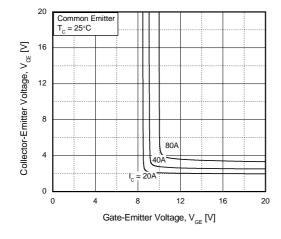


Figure 2. Typical Saturation Voltage Characteristics

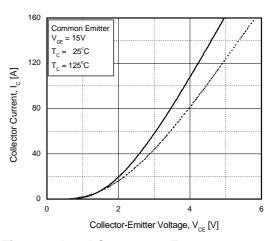


Figure 4. Load Current vs. Frequency

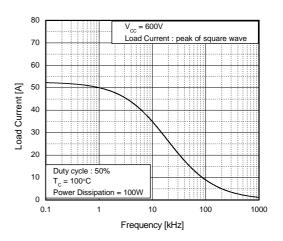
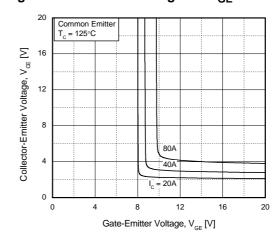


Figure 6. Saturation Voltage vs. V<sub>GE</sub>



## Typical Performance Characteristics (Continued)

Figure 7. Capacitance Characteristics

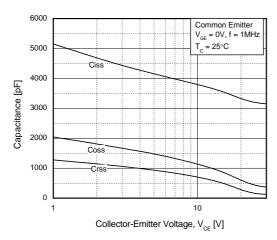


Figure 9. Turn-Off Characteristics vs. **Gate Resistance** 

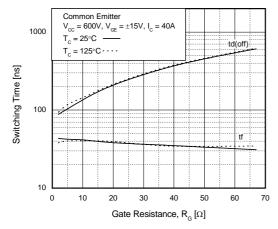


Figure 11. Turn-On Characteristics vs. **Collector Current** 

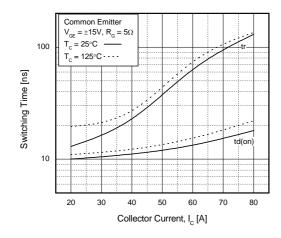


Figure 8. Turn-On Characteristics vs. Gate Resistance

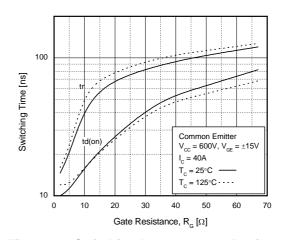


Figure 10. Switching Loss vs. Gate Resistance

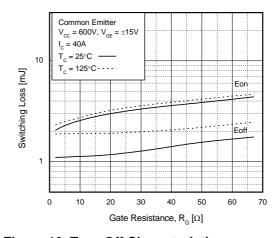
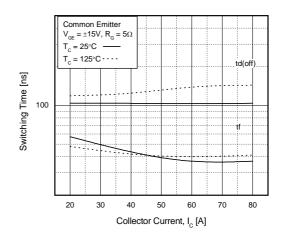


Figure 12. Turn-Off Characteristics vs. **Collector Current** 



## Typical Performance Characteristics (Continued)

Figure 13. Switching Loss vs. Collector Current

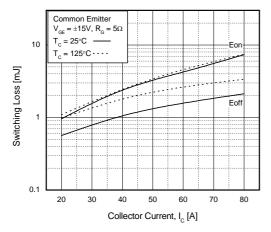


Figure 14. Gate Charge Characteristics

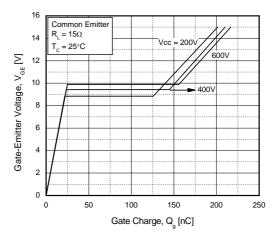


Figure 15. SOA Characteristics

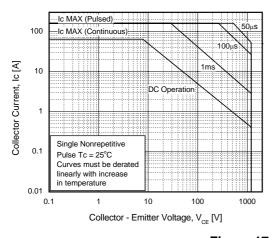


Figure 16. Turn-Off SOA

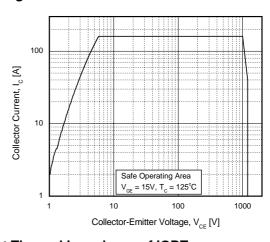
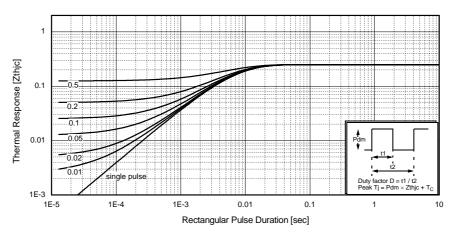
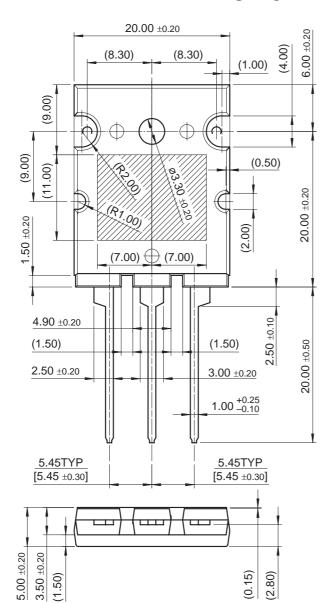


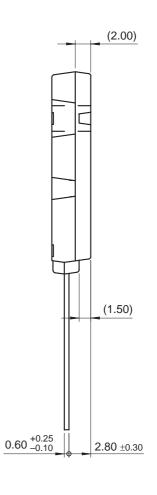
Figure 17. Transient Thermal Impedance of IGBT



## **Mechanical Dimensions**

TO-264





Dimensions in Millimeters





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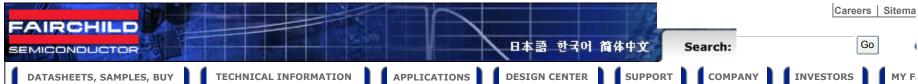
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## FGL40N120AN

1200V NPT IGBT

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- Features
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#### **General description**

Employing NPT technology, Fairchild's AN series of IGBTs provides low conduction and switching losses. The AN series offers an solution for application such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).

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#### **Features**

- High speed switching
- Low saturation voltage: V<sub>CE(sat)</sub> = 2.6 V @ I<sub>C</sub> = 40A
- High input impedance

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#### **Applications**

Induction Heating, UPS, AC & DC motor controls and general purpose inverters.

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Product status/pricing/packaging

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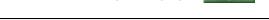
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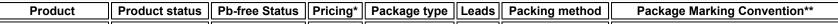
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Sales support

Quality and reliability

Design center





FGL40N120ANTU	Full Production	Full Production	\$10.78	<u>TO-264</u>	3	RAIL	Line 1: <b>\$Y</b> (Fairchild logo) & <b>Z</b> (Asm. Plant Code) &E Line 2: FGL40N120 Line 3: AN &3
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<sup>\*</sup> Fairchild 1,000 piece Budgetary Pricing

\*\* A sample button will appear if the part is available through Fairchild's on-line samples program. If there is no sample button, please contact a Fairchild distributor to obtain samples



Indicates product with Pb-free second-level interconnect. For more information click here.

Package marking information for product FGL40N120AN is available. Click here for more information.

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